

**IN THE SPECIFICATION:**

(a) Page 13, delete entire paragraph starting in line 21 and replace it with the following new paragraph:

- - Furthermore, an oxygen film is formed on a surface of this silicon wafer W by performing the thermal processing operation in an oxygen (~~O<sub>2</sub>~~) (O<sub>2</sub>) gas atmosphere at a temperature which is not greater than 950°C; thus, it is possible to obtain a silicon wafer of which surface quality is improved. - -